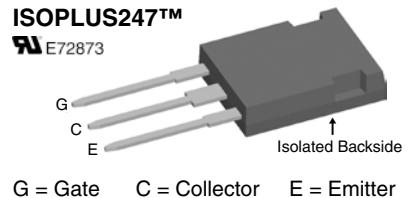
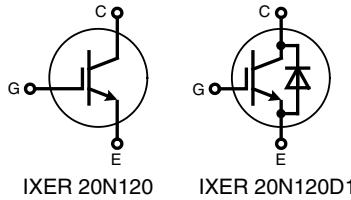


## NPT<sup>3</sup> IGBT

in ISOPLUS247™

**I<sub>C25</sub>** = 36 A  
**V<sub>CES</sub>** = 1200 V  
**V<sub>CE(sat)typ</sub>** = 2.4 V



### IGBT

Symbol	Conditions	Maximum Ratings		
<b>V<sub>CES</sub></b>	T <sub>VJ</sub> = 25°C to 150°C	1200	V	
<b>V<sub>GES</sub></b>		± 20	V	
<b>I<sub>C25</sub></b>	T <sub>C</sub> = 25°C	29	A	
<b>I<sub>C90</sub></b>	T <sub>C</sub> = 90°C	19	A	
<b>I<sub>CM</sub></b> <b>V<sub>CEK</sub></b>	V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 68 Ω; T <sub>VJ</sub> = 125°C RBSOA Clamped inductive load; L = 100 μH	40	A	V <sub>CES</sub>
<b>t<sub>SC</sub></b> <b>(SCSOA)</b>	V <sub>CE</sub> = 900 V; V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 68 Ω T <sub>VJ</sub> = 125°C; non-repetitive	10	μs	
<b>P<sub>tot</sub></b>	T <sub>C</sub> = 25°C	130	W	

### Symbol      Conditions      Characteristic Values

(T<sub>VJ</sub> = 25°C, unless otherwise specified)

		min.	typ.	max.	
<b>V<sub>CE(sat)</sub></b>	I <sub>C</sub> = 20 A; V <sub>GE</sub> = 15 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		2.4 2.8	2.8	V V
<b>V<sub>GE(th)</sub></b>	I <sub>C</sub> = 0.6 mA; V <sub>GE</sub> = V <sub>CE</sub>	4.5		6.5	V
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>GE</sub> = 0 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		0.2 0.2	0.2	mA mA
<b>I<sub>GES</sub></b>	V <sub>CE</sub> = 0 V; V <sub>GE</sub> = ± 20 V			200	nA
<b>t<sub>d(on)</sub></b> <b>t<sub>r</sub></b> <b>t<sub>d(off)</sub></b> <b>t<sub>f</sub></b> <b>E<sub>on</sub></b> <b>E<sub>off</sub></b>	Inductive load L = 100 μH; T <sub>VJ</sub> = 125°C V <sub>CE</sub> = 600 V; I <sub>C</sub> = 25 A V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 68 Ω		205 105 320 175 4.1 1.5		ns ns ns ns mJ mJ
<b>C<sub>ies</sub></b> <b>Q<sub>Gon</sub></b>	V <sub>CE</sub> = 25 V; V <sub>GE</sub> = 0 V; f = 1 MHz V <sub>CE</sub> = 600 V; V <sub>GE</sub> = 15 V; I <sub>C</sub> = 20 A		1.2 100		nF nC
<b>R<sub>thJC</sub></b> <b>R<sub>thCH</sub></b>	with heatsink compound		0.5	0.96	K/W K/W

### Features

- NPT<sup>3</sup> IGBT
  - low saturation voltage
  - positive temperature coefficient for easy paralleling
  - fast switching
  - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diode
  - fast reverse recovery
  - low operating forward voltage
  - low leakage current
- ISOPLUS247™ package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - high reliability
  - industry standard outline

### Applications

- single switches
- choppers with complementary free wheeling diodes
- phaselegs, H bridges, three phase bridges e.g. for
  - power supplies, UPS
  - AC, DC and SR drives
  - induction heating

## Diode [D1 version only]

Symbol	Conditions	Maximum Ratings		
$I_{F25}$	$T_C = 25^\circ\text{C}$	25	A	
$I_{F90}$	$T_C = 90^\circ\text{C}$	15	A	

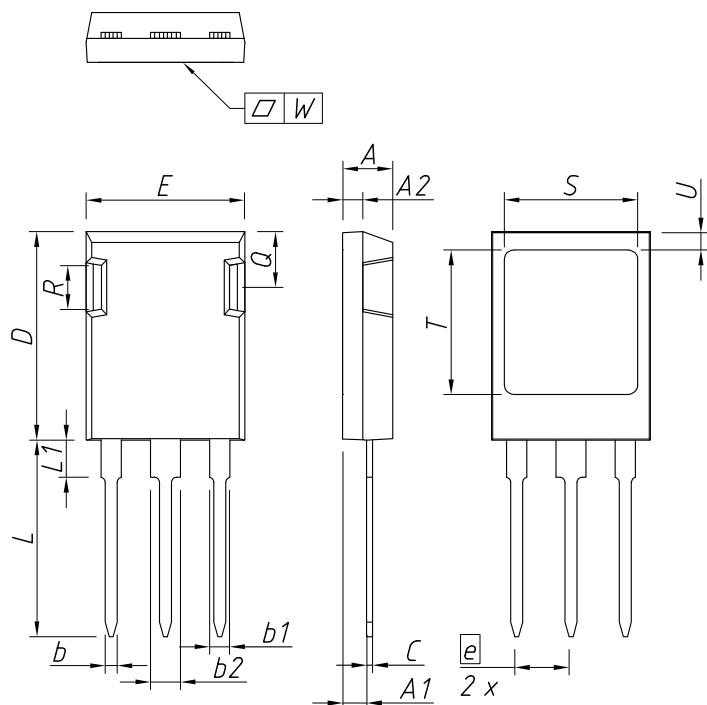
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$V_F$	$I_F = 20 \text{ A}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.6 2.0	3.0	V
$I_{RM}$ $t_{rr}$	$\left. \begin{array}{l} V_R = 600 \text{ V}; L = 100 \mu\text{H}; T_{VJ} = 125^\circ\text{C} \\ dI_F/dt = -400 \text{ A}/\mu\text{s}; I_F = 15 \text{ A}; V_{GE} = 0 \text{ V} \end{array} \right\}$		16 130		A ns
$R_{thJC}$ $R_{thCH}$	with heatsink compound		2.3 1.3		K/W

## Module

Symbol	Conditions	Maximum Ratings		
$T_{VJ}$		-55...+150	$^\circ\text{C}$	
$T_{stg}$		-55...+150	$^\circ\text{C}$	
$V_{ISOL}$	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~	
$F_c$	mounting force with clip	20...120	N	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$C_p$	coupling capacity between shorted pins and mounting tab in the case		30	pF
Weight			6	g

## ISOPLUS247™ Outline



DIM.	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,29	2,54	0,090	0,100
A2	1,91	2,16	0,075	0,085
b	1,14	1,40	0,045	0,055
b1	1,91	2,15	0,075	0,085
b2	2,92	3,20	0,115	0,126
C	0,61	0,83	0,024	0,033
D	20,80	21,34	0,819	0,840
E	15,75	16,13	0,620	0,635
e	5,45 BSC		0,215 BSC	
L	19,81	20,60	0,780	0,811
L1	3,81	4,38	0,150	0,172
Q	5,59	6,20	0,220	0,244
R	4,32	4,85	0,170	0,191
S	13,21	13,72	0,520	0,540
T	15,75	16,26	0,620	0,640
U	1,65	2,03	0,065	0,080
W	-	0,10	-	0,004

Die konvexe Form des Substrates ist typ. < 0,04 mm über der Kunststoffoberfläche der Bauteilunterseite  
The convex bow of substrate is typ. < 0,04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und  $L_{max}$ .  
This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except  $L_{max}$ .

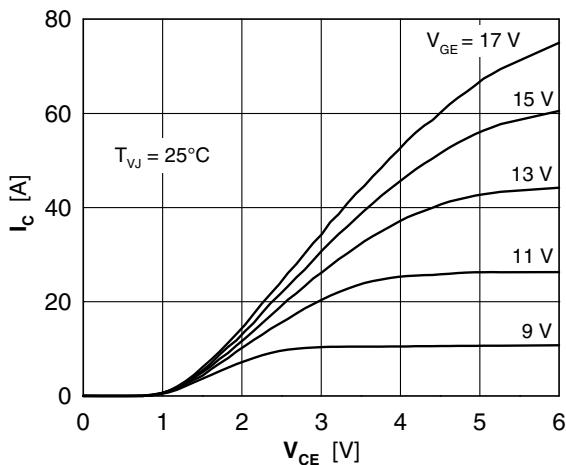


Fig. 1 Typ. output characteristics

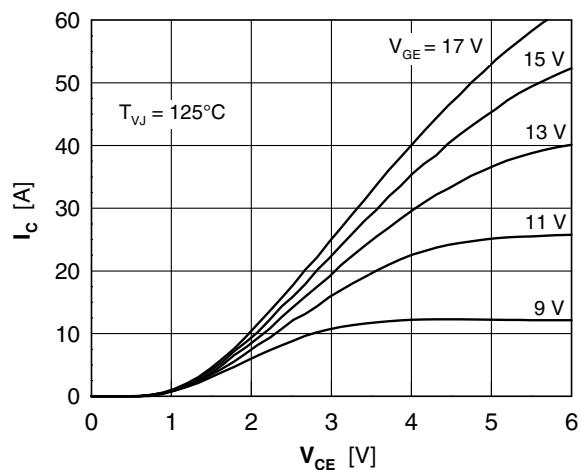


Fig. 2 Typ. output characteristics

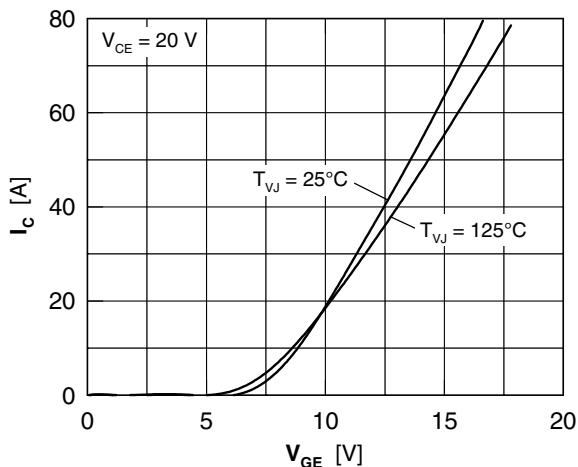


Fig. 3 Typ. transfer characteristics

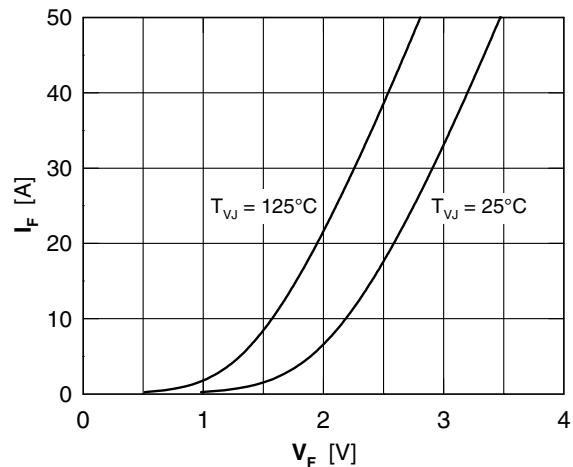


Fig. 4 Typ. forward characteristics  
of free wheeling diode

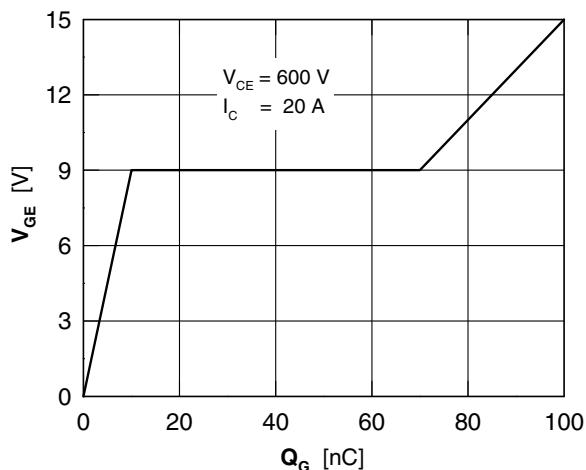


Fig. 5 Typ. turn on gate charge

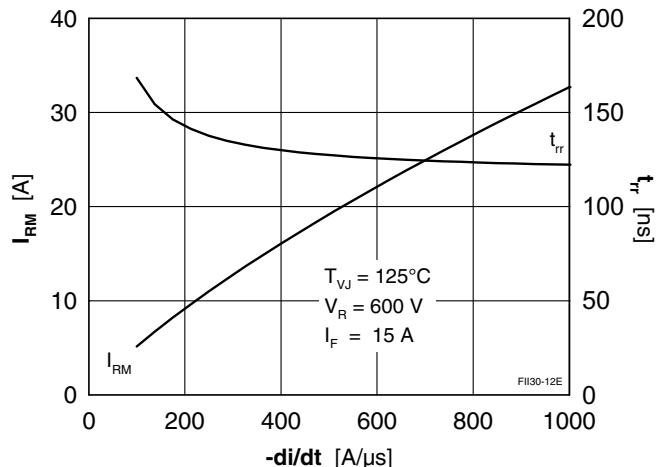


Fig. 6 Typ. turn off characteristics  
of free wheeling diode

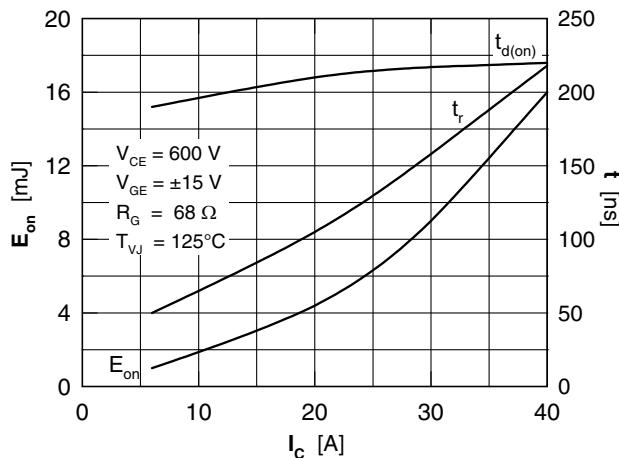


Fig. 7 Typ. turn on energy and switching times versus collector current

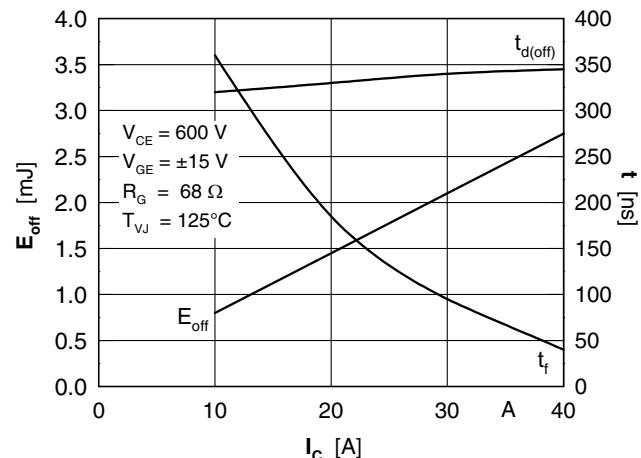


Fig. 8 Typ. turn off energy and switching times versus collector current

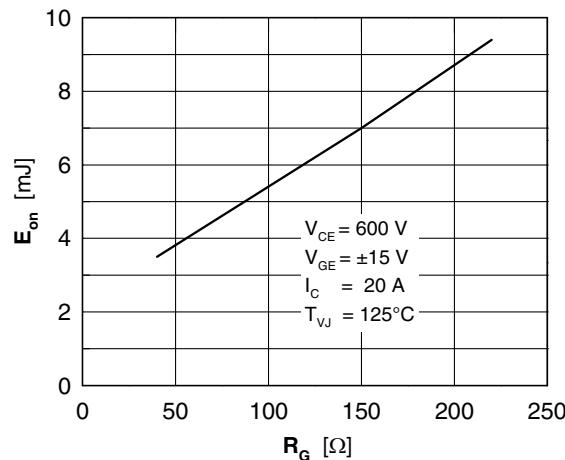


Fig. 9 Typ. turn on energy vs gate resistor

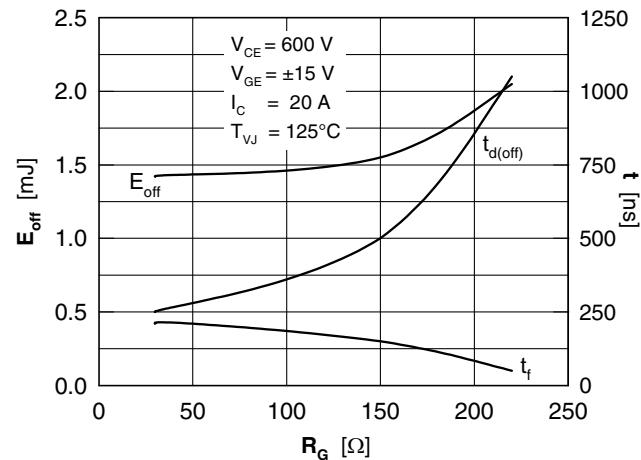


Fig. 10 Typ. turn off energy and switching times versus gate resistor

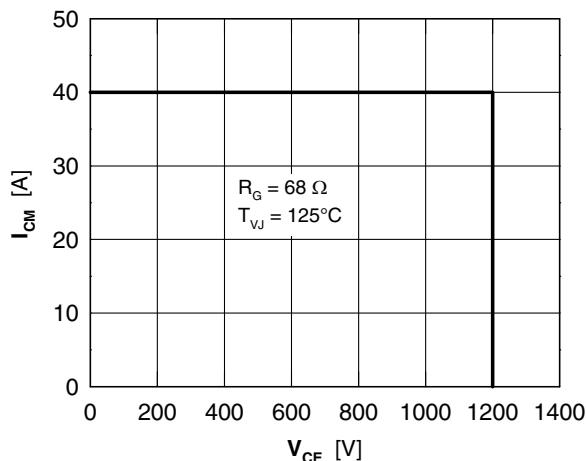


Fig. 11 Reverse biased safe operating area  
RBSOA

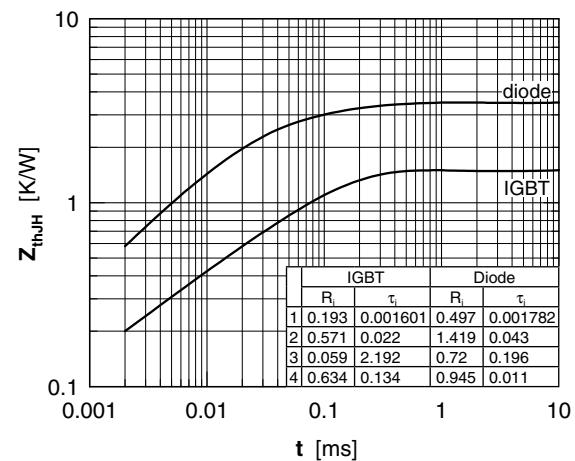


Fig. 12 Typ. transient thermal impedance

IXYS reserves the right to change limits, test conditions and dimensions.

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#### Thermal Analysis Model

$$Z_{th}(t) = \sum_{i=1}^n \left[ R_i \cdot \left( 1 - \exp \left( -\frac{t}{\tau_i} \right) \right) \right]$$